## K. J. Somaiya Institute of Technology, Sion, Mumbai-22 (Autonomous College Affiliated to University of Mumbai)

April-May 2023 (B.Tech)

Examination: SY Semester: III

Course Code: EXC303

Course Name: Electronic Devices and Circuits

Duration: 2.5 Hours

Max. Marks: 60

Date of Exam: 30/05/2023

Instructions:

(1)All questions are compulsory.

(2)Draw neat diagrams wherever applicable. (3)Assume suitable data, if necessary.

|       |   | Max.<br>Marks | СО | BT<br>level |
|-------|---|---------------|----|-------------|
| Q 1   | Solve any six questions out of eight:   | 12            |    |             |
| i)    | Describe the channel length modulation effect and define the parameter.   | 2             | 1  | U           |
| ii)   | Which factor decreases gain of amplifier at lower frequency? Explain.   | 2             | 2  | U           |
| iii)  | Write transfer function of RC high pass filter.   | 2             | 1  | U           |
| iv)   | Write down the expression of $V_{\text{GS}}$ in terms of $I_{\text{Dsat}}$ if nmos transistor is in saturation region.  | 2             | 3  | U           |
| v)    | State expression of diode voltage in terms of diode current.  | 2             | 4  | R           |
| vi)   | Define CMRR.  | 2             | 5  | R           |
| vii)  | State expression for Vo for differentia amplifier.  | 2             | 6  | U           |
| viii) | Draw n channel EMOSFET cross section diagram for $V_{GS} < V_{TN}$ showing channel area clearly.  | 2             | 2  |             |
| Q.2   | Solve any four questions out of six.  | 16            |    |             |
| i)    | Calculate the drain current in an NMOS transistor with parameters $V_{TN}$ = 0.8 V, k'n =80 $\mu$ A/V², W = 10 $\mu$ m, L = 1.2 $\mu$ m, and with applied voltages of $V_{DS}$ = 0.1 V and (a) $V_{GS}$ = 0, (b) $V_{GS}$ = 1 V, (c) $V_{GS}$ = 2.5 V | 4             | 1  | AP          |
| ii)   | How does a transistor width-to-length ratio affect the small-signal voltage gain of a common-source amplifier?  | 4             | 3  | U           |
| iii)  | Describe the channel length modulation effect and define the parameter $\lambda$ .  | 4             | 4  | U           |
| iv)   | Explain effect of Miller capacitance.   | 4             | 2  | U           |
| v)    | Explain the effect of $R_{\text{sig}}$ and $R_{\text{L}}$ on the amplifier gain.  | 4             | 5  | U           |
| vi)   | Describe an amplifier system with one application as Example.   | 4             | 6  | U           |
| Q.3   | Solve any two questions out of three.   | 16            |    |             |

## K. J. Somaiya Institute of Technology, Sion, Mumbai-22 (Autonomous College Affiliated to University of Mumbai)

| i)   | Discuss, using the concept of a load line superimposed on the transistor characteristics, how a simple common-source circuit can amplify a time-varying signal.  | 8  | 1 | U  |          |
|------|--|----|---|----|----------|
| ii)  | Draw high frequency equivalent circuit model for nmos.   | 8  | 2 | U  | $\dashv$ |
| iii) | Explain MOSFET I-V characteristic in details and state expression for small signal parameter.  | 8  | 3 | U  |          |
| Q.4  | Solve any two questions out of three.  | 16 |   |    | +        |
| i)   | How does a transistor width-to-length ratio affect the small-signal voltage gain of a common-source amplifier? Explain by deriving gain of amplifier.  | 8  | 5 | U  |          |
| ii)  | The circuit in Figure is to be used as a simple audio amplifier. Find lower corner frequency if Cc=0.477uF and Cc1=1uF. $R_D = 6.7 \text{ k}\Omega$ $R_C = \frac{1}{5} \text{ k}\Omega$ $R_C = \frac{1}{5} \text{ k}\Omega$ $R_C = \frac{1}{5} \text{ k}\Omega$    | 8  | 4 | AP |          |
| ii)  | In the circuit in Figure below the transistor parameters are $V_{TN}$ = 0.8 V and $K_n$ = 0.5 mA/V². Calculate $V_{GS}$ , $I_{D}$ , and $V_{DS}$ . $ V_{DD} = 10 \text{ V} $ $ R_1 = 32 \text{ k}\Omega $ $ R_2 = 18 \text{ k}\Omega $ $ R_S = 2 \text{ k}\Omega $ | 8  | 6 | AP |          |